

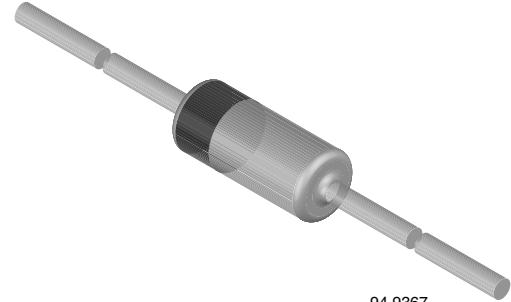
Small Signal Switching Diode

Features

- Silicon Epitaxial Planar Diode
- AEC-Q101 qualified
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



RoHS
COMPLIANT
HALOGEN
FREE



94 9367

Applications

- Extreme fast switches

Mechanical Data

Case: DO-35

Weight: approx. 125 mg

Cathode Band Color: black

Packaging Codes/Options:

TR/10 k per 13" reel (52 mm tape), 50 k/box

TAP/10 k per Ammopack (52 mm tape), 50 k/box

Parts Table

Part	Ordering code	Type Marking	Remarks
BAW75	BAW75-TR or BAW75-TAP	BAW75	Tape and Reel/Ammopack

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V_{RRM}	35	V
Reverse voltage		V_R	25	V
Peak forward surge current	$t_p = 1\text{ }\mu\text{s}$	I_{FSM}	2000	mA
Repetitive peak forward current		I_{FRM}	450	mA
Forward continuous current		I_F	300	mA
Average forward current	$V_R = 0$	I_{FAV}	150	mA
Power dissipation	$l = 4\text{ mm}, T_L = 45\text{ }^{\circ}\text{C}$	P_{tot}	440	mW
	$l = 4\text{ mm}, T_L \leq 25\text{ }^{\circ}\text{C}$	P_{tot}	500	mW

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

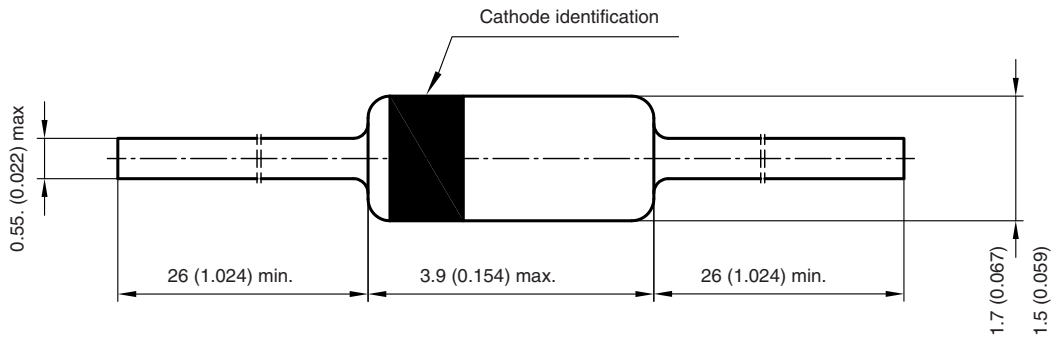
Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	$l = 4\text{ mm}, T_L = \text{constant}$	R_{thJA}	350	K/W
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 30\text{ mA}$	V_F			1000	mV
Reverse current	$V_R = 25\text{ V}$	I_R			100	nA
	$V_R = 25\text{ V}, T_j = 150\text{ }^{\circ}\text{C}$	I_R			100	μA
Breakdown voltage	$I_R = 5\text{ }\mu\text{A}, t_p/T = 0.01,$ $t_p = 0.3\text{ ms}$	$V_{(BR)}$	35			V
Diode capacitance	$V_R = 0, f = 1\text{ MHz},$ $V_{HF} = 50\text{ mV}$	C_D			4	pF
Reverse recovery time	$I_F = I_R = 10\text{ mA}, I_R = 1\text{ mA}$	t_{rr}			4	ns
	$I_F = 10\text{ mA}, V_R = 6\text{ V},$ $I_R = 1\text{ mA}, R_L = 100\text{ }\Omega$	t_{rr}			2	ns

Package Dimensions in millimeters (inches): DO-35



Rev. 6 - Date: 29. January 2007
 Document no.: 6.560-5004.02-4
 94 9366



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